



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage 60 V Current 2.5 A

#### **Features**

- RDS(ON), VGS@10V, ID@2.0A<75mΩ
- RDS(ON), VGS@4.5V, ID@1.0A<90mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

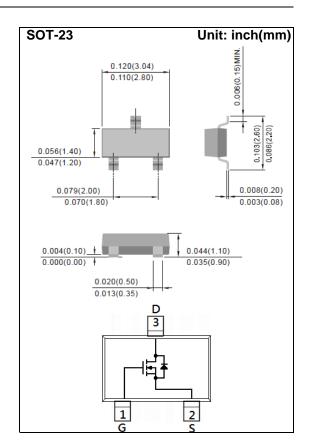
#### **Mechanical Data**

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking: A60



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	2.5	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	10	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	100	°C/W





# Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.75	2.5	V		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A	-	55	75	mΩ		
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A	-	63	90			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	uA		
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 5)								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =48V, I <sub>D</sub> =2.0A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	9.3	-	nC		
Gate-Source Charge	$Q_gs$		-	2.2	-			
Gate-Drain Charge	$Q_gd$		-	1.9	-			
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	509	-	pF		
Output Capacitance	Coss		-	47	-			
Reverse Transfer Capacitance	Crss		-	23	-			
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =30V, $I_{D}$ =2.0A, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ (Note 1,2)	-	3.2	-			
Turn-On Rise Time	tr		-	9.7	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	18.5	-			
Turn-Off Fall Time	tf		-	6.4	-			
Drain-Source Diode								
Maximum Continuous Drain-Source			-	-	2.5	А		
Diode Forward Current	I <sub>S</sub>							
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.77	1.2	V		

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

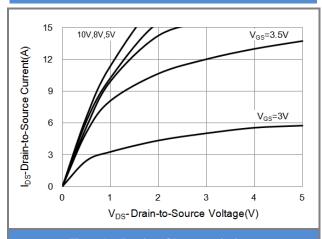
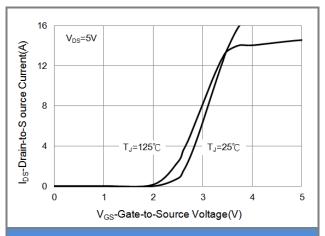


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

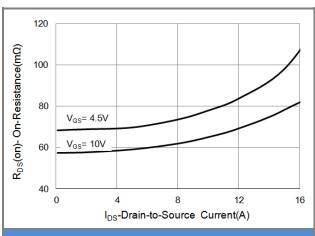


Fig.3 On-Resistance vs. Drain Current

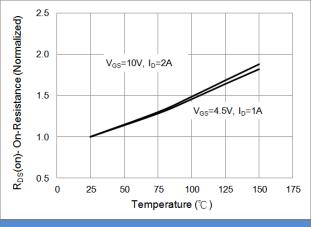
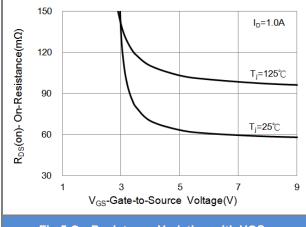
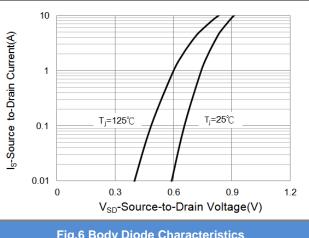


Fig.4 On-Resistance vs. Junction temperature







**Fig.6 Body Diode Characteristics** 





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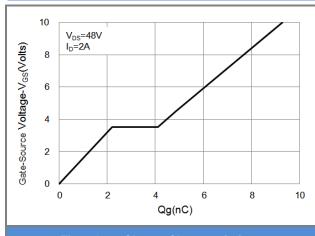


Fig.7 Gate-Charge Characteristics

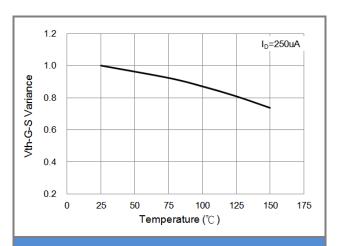


Fig.8 Threshold Voltage Variation with Temperature.

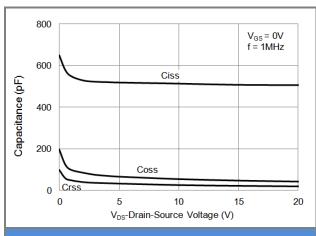


Fig.9 Capacitance vs. Drain-Source Voltage.

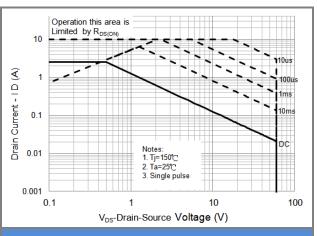
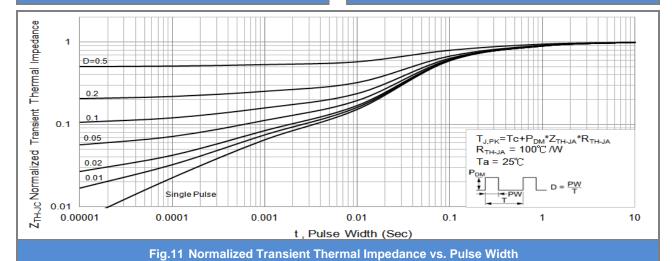


Fig.10 Maximum Safe Operating Area.



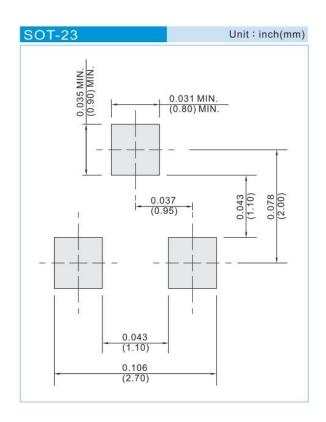




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type	Marking	Version
PJA3460_R1_00001	SOT-23	3K pcs / 7" reel	A60	Halogen free
PJA3460_R2_00001	SOT-23	12K pcs / 13" reel	A60	Halogen free

### **MOUNTING PAD LAYOUT**







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